

List of Final Projects

10.16.2003

Groups 1 and 2

Group 1

Title: GaN Substrate Transistors

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Group 2:

Title: Semiconductor Device and Circuits for
Broadband Data Transfer. Existing Solutions.
Challenges and trends.

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Groups 3 and 4

Group 3

Title: Interconnect Bottleneck in VLSI. The problem and possible solutions

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Group 4

Title: High Temperature Limits for Silicon VLSI

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Groups 5 and 6

Group 5

Title: Parameters of Digital Circuits

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Group 6

Title: Organic Transistors

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Groups 7 and 8

Group 7

Title: Quantum Well Structure in GaN LED

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Group 8

Title: GaN FETs

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Group 9 and not assigned

Group 9

Title: Modelling of Short Channel Behaviour in
MOSFETs

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Group 10

Title: Electromigration of Cu interconnects

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Long distance students

Group 10

Title: Scaling of Si MOSFETs for Digital Applications

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Group 11:

Title: of Si MOSFETs for Digital Applications

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Groups 12 and 13

Group 12

Title: Diamond Transistors

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Group 13

Title: Power Transistors

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Groups 14 and 15

Group 14

Title: Carbon Nanotubes and the Future of
Nanoelectronics

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Group 15

Title: Si MOSFETs for Analog Applications

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Groups 16 and 17

Group 16

Title: Raised Source/Drain Architecture in CMOS devices

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Group 17

Title: CMOS Device Scaling

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Groups 18 and 19

Group 18

Title: GaN HEMT in RF and power application

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Group 19

Title: Baliga-pair Structures

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